L Number	Hits	Search Text	DB	Time stamp
1	1099	438/127.ccls.	USPAT;	2004/09/15 11:36
			US-PGPUB;	
	İ		EPO; JPO;	
			DERWENT;	
		•	IBM_TDB	
2	1505	438/780.ccls.	USPAT;	2004/09/15 11:37
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		•	IBM_TDB	
3	1645	semiconductor same underfill	USPAT;	2004/09/15 12:17
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	91	438/127.ccls. and (semiconductor same	USPAT;	2004/09/15 11:37
		underfill)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	200		IBM_TDB	
6	228	semiconductor same underfill same reflow	USPAT;	2004/09/15 11:41
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
7	10	420/127	IBM_TDB	0004/00/45 40 45
'	12	438/127.ccls. and (semiconductor same underfill same reflow)	USPAT;	2004/09/15 12:16
		underlil same reliow)	US-PGPUB;	
			EPO; JPO; DERWENT;	
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8	390	(525/117 525/114).ccls.	IBM_TDB USPAT;	2004/09/15 12:16
"	3,0	(323/117 323/1147.0018.	US-PGPUB;	2004/03/13 12:16
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
9	83170	maleic adj anhydride	USPAT;	2004/09/15 12:16
	332.13		US-PGPUB;	2004,03,13 12.10
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
10	140	(maleic adj anhydride) and ((525/117	USPAT;	2004/09/15 12:17
		525/114).ccls.)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
11	3066478	semiconductor or printed adj circuit or	USPAT;	2004/09/15 12:17
		electronic	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
12		(/malaia - 3ih3-i 3-) 3 (/coc/r	IBM_TDB	
12	21	((maleic adj anhydride) and ((525/117	USPAT;	2004/09/15 12:17
		525/114).ccls.)) and (semiconductor or	US-PGPUB;	
		printed adj circuit or electronic)	EPO; JPO;	
			DERWENT;	
13	20016	norbornene	<pre>IBM_TDB USPAT;</pre>	2004/00/15 12 13
10	20010	HOLDOLINGHE	USPAT; US-PGPUB;	2004/09/15 12:17
		•		
		ç	EPO; JPO; DERWENT;	
		`	IBM TDB	
14	1	(((maleic adj anhydride) and ((525/117	USPAT;	2004/09/15 12:18
		525/114).ccls.)) and (semiconductor or	US-PGPUB;	2004/03/13 12:18
		printed adj circuit or electronic)) and	EPO; JPO;	
		norbornene	DERWENT;	
			IBM TDB	
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